

Notice of References Cited	Application/Control No. 10/006,704	Applicant(s)/Patent Under Reexamination TRAPP, SHANE J.	
	Examiner Lynette T. Umez-Eronini	Art Unit 1765	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-5,935,877	08-1999	Autryve, Luc Van	438/743
	C	US-			
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

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	N	JP 54054578A	04-1979	Japan	Yamagishi et al.	H01L 21/302
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NON-PATENT DOCUMENTS

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	U	Yamagishi et al., Gas Plasma Etching Method, April 29, 1979, English Abstract of JP 54054578 A, 3 pages.
	V	Smolinsky et al., Reactive Ion Etching of Silicon Oxides with Ammonia and Trifluoromethane. The Role of Nitrogen in the Discharge, J. Electrochem. Soc.: SOLID-STATE SCIENCE AND TECHNOLOGY, No. 5, Vol. 129, May 1982, pp. 1036-1039.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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